

**CPH5818****DC / DC Converter Applications****Features**

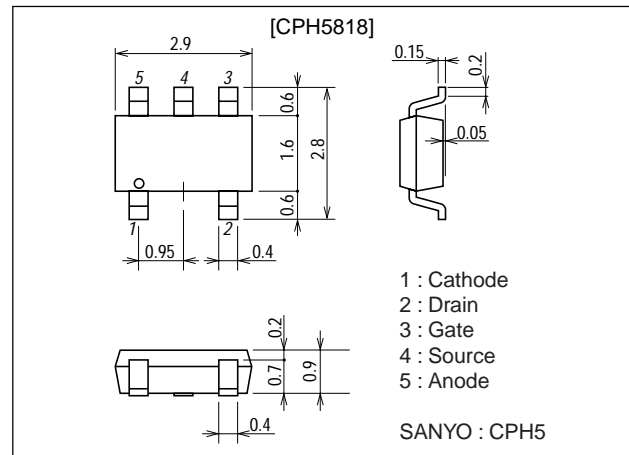
- Composite type with a P-Channel Silicon MOSFET (MCH3339) and a Schottky Barrier Diode (SBS007M) contained in one package facilitating high-density mounting.

[MOSFET]

- Low ON-resistance.
- Ultrahigh-speed switching.

[SBD]

- Short reverse recovery time.
- Low forward voltage.

Package Dimensionsunit : mm
2171**Specifications****Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V _{DSS}		-12	V
Gate-to-Source Voltage	V _{GS}		±12	V
Drain Current (DC)	I _D		-1.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-6.0	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (600mm ² X0.8mm) 1unit	0.8	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V _R RM		15	V
Nonrepetitive Peak Reverse Surge Voltage	V _R SM		15	V
Average Output Current	I _O		0.5	A
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	3	A
Junction Temperature	T _J		-55 to +125	°C
Storage Temperature	T _{stg}		-55 to +125	°C

Marking : QU

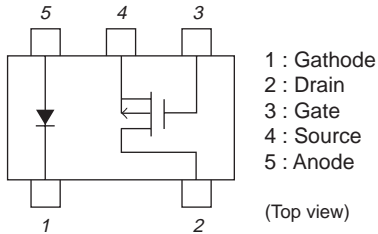
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Electrical Characteristics at Ta=25°C

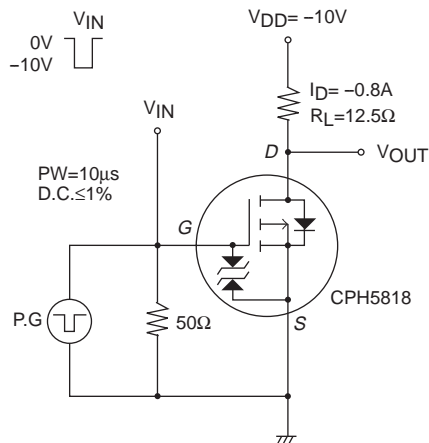
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-12			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 9.6V, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -6V, I_D = -1mA$	-1.0		-2.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -6V, I_D = -0.8A$	0.9	1.4		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -0.8A, V_{GS} = -10V$		200	270	m Ω
	$R_{DS(on)2}$	$I_D = -0.4A, V_{GS} = -4.5V$		340	490	m Ω
	$R_{DS(on)3}$	$I_D = -0.1A, V_{GS} = -4V$		370	530	m Ω
Input Capacitance	C_{iss}	$V_{DS} = -6V, f = 1MHz$		145		pF
Output Capacitance	C_{oss}	$V_{DS} = -6V, f = 1MHz$		45		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -6V, f = 1MHz$		35		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		7.5		ns
Rise Time	t_r	See specified Test Circuit		20		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		16		ns
Fall Time	t_f	See specified Test Circuit		12		ns
Total Gate Charge	Q_g	$V_{DS} = -10V, V_{GS} = -10V, I_D = -1.5A$		3.8		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -10V, V_{GS} = -10V, I_D = -1.5A$		0.5		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS} = -10V, V_{GS} = -10V, I_D = -1.5A$		0.5		nC
Diode Forward Voltage	V_{SD}	$I_S = -1.5A, V_{GS} = 0$		-0.94	-1.5	V
[SBD]						
Reverse Voltage	V_R	$I_R = 0.5mA$	15			V
Forward Voltage	V_{F1}	$I_F = 0.3A$		0.35	0.41	V
	V_{F2}	$I_F = 0.5A$		0.4	0.46	V
Reverse Current	I_R	$V_R = 6V$			200	μA
Interterminal Capacitance	C	$V_R = 10V, f = 1MHz$ cycle		20		pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 100mA$, See specified Test Circuit.			10	ns

Electrical Connection



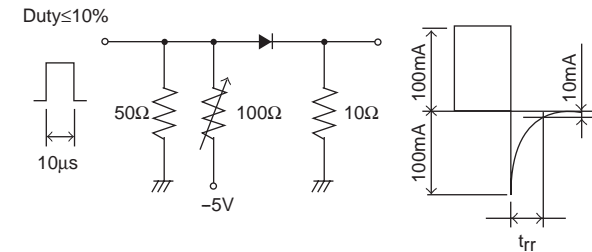
Switching Time Test Circuit

[MOSFET]

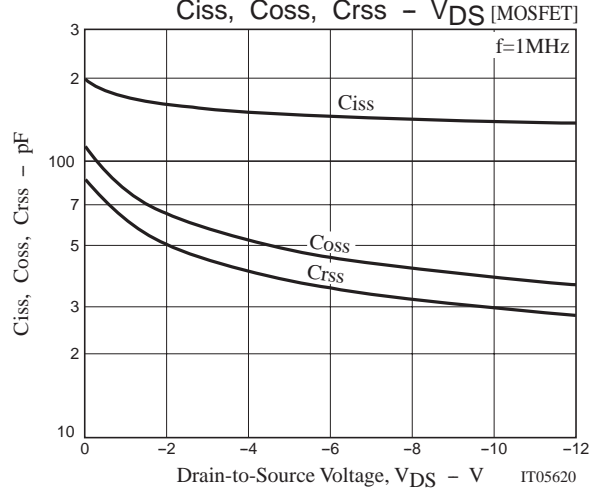
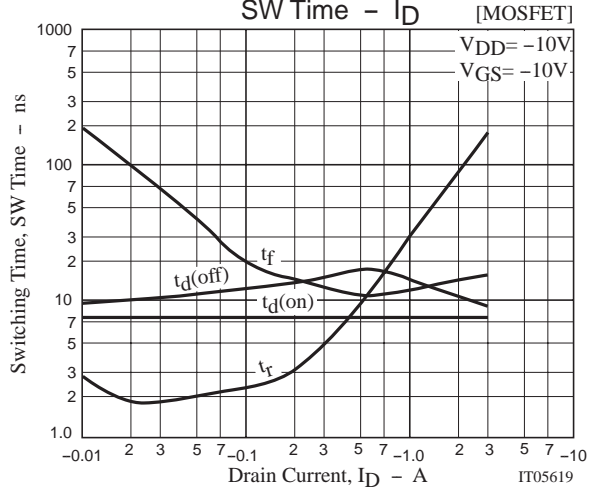
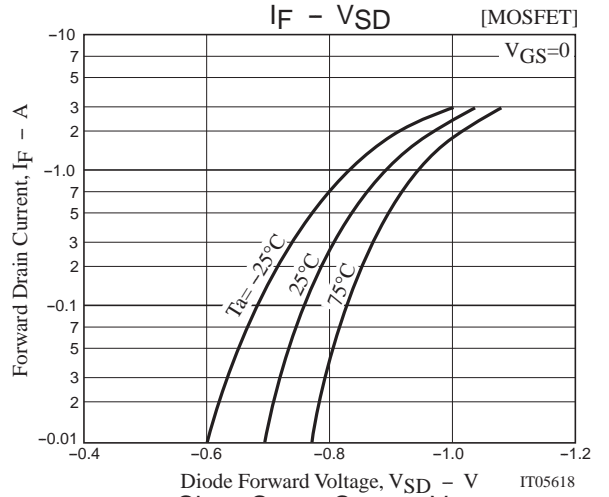
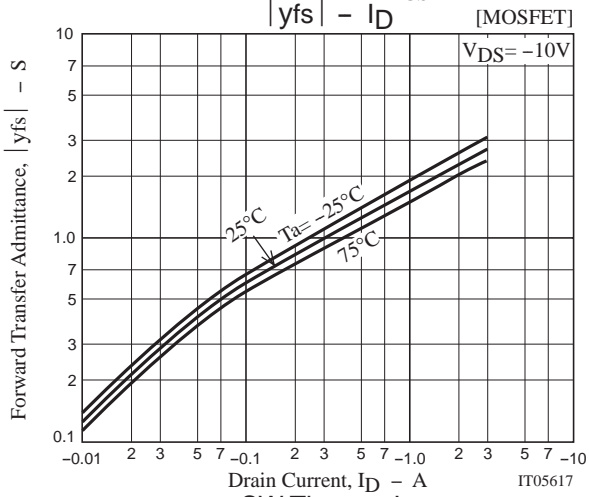
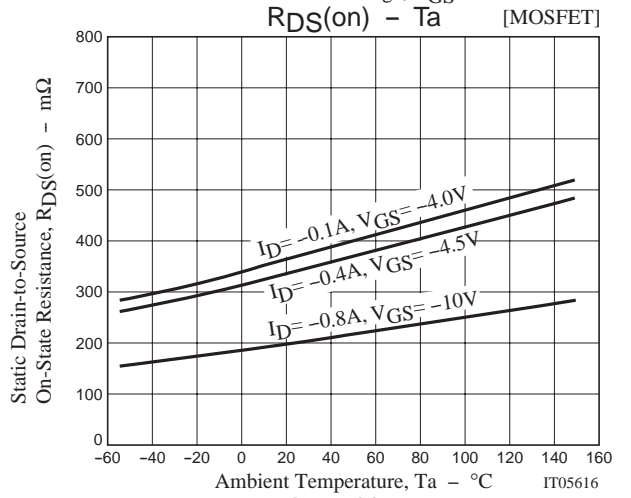
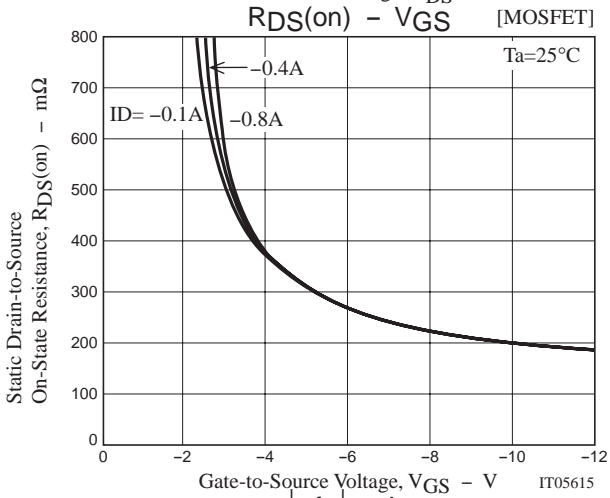
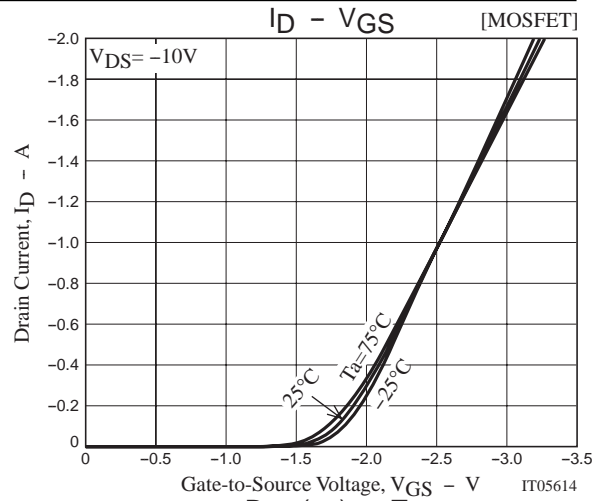
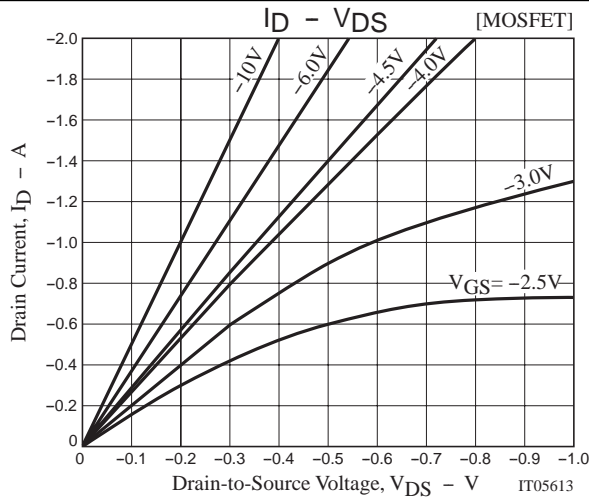


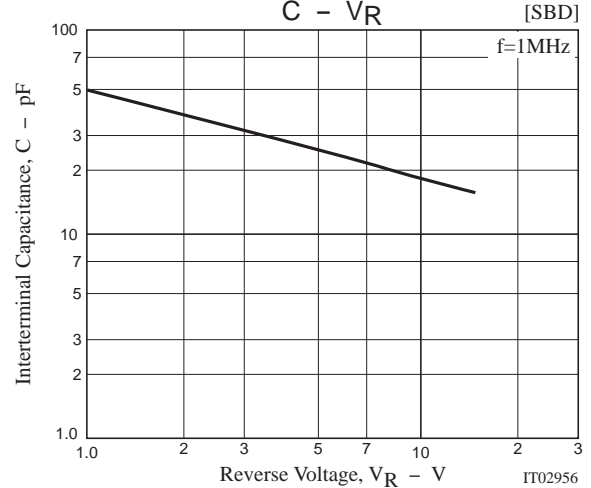
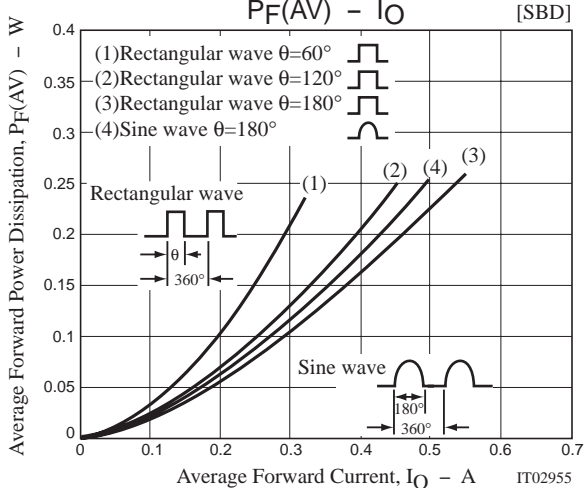
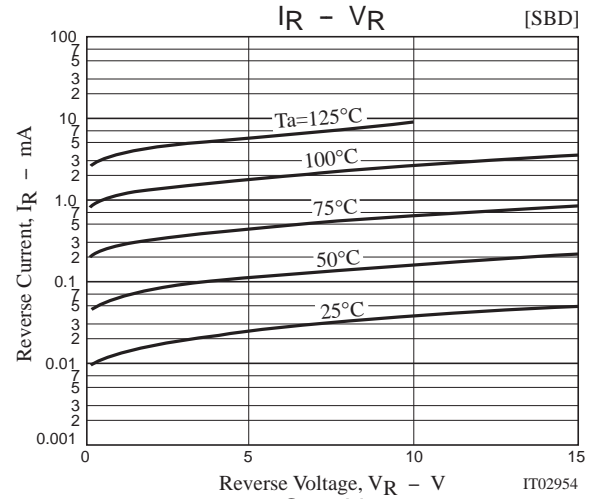
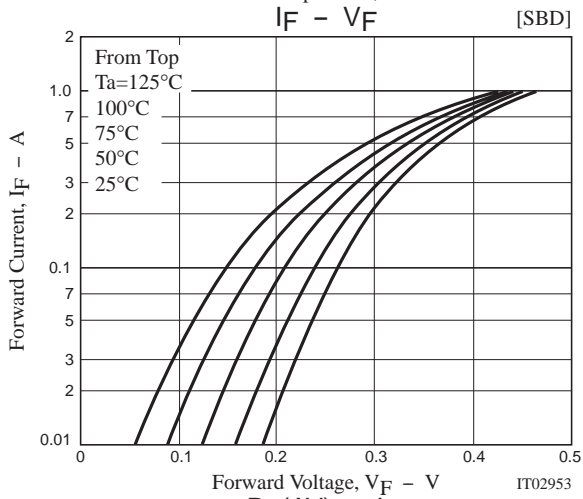
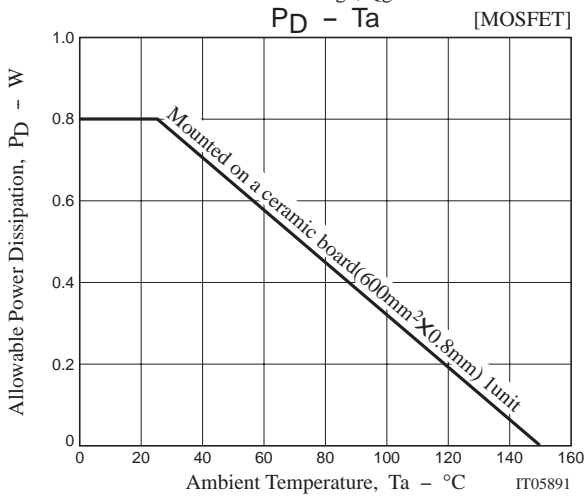
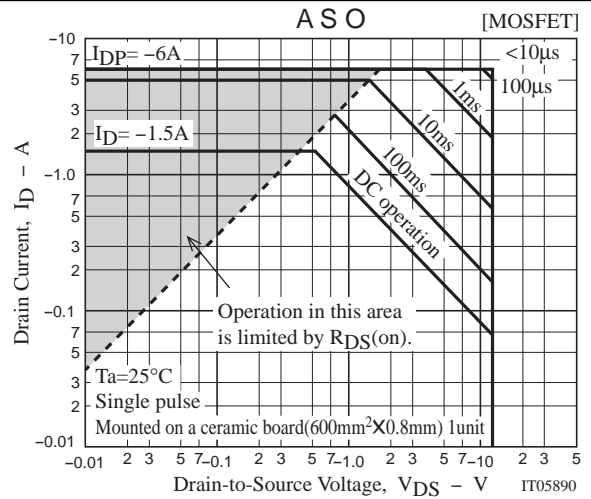
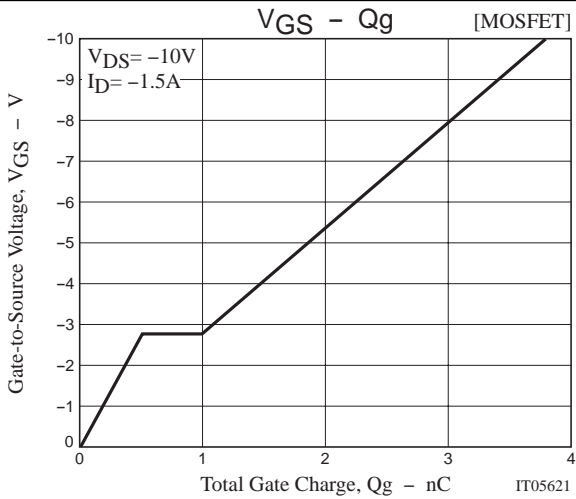
trr Test Circuit

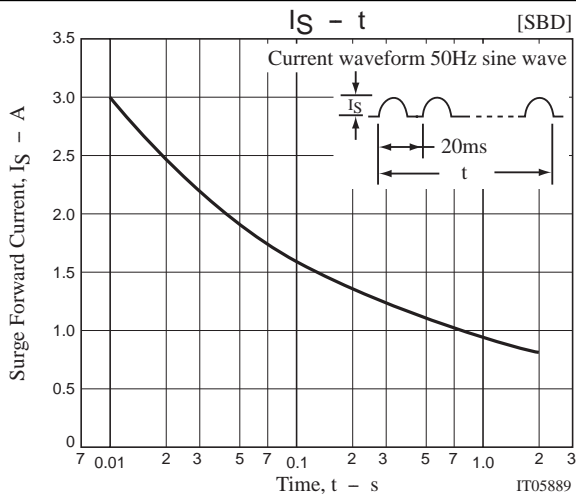
[SBD]



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